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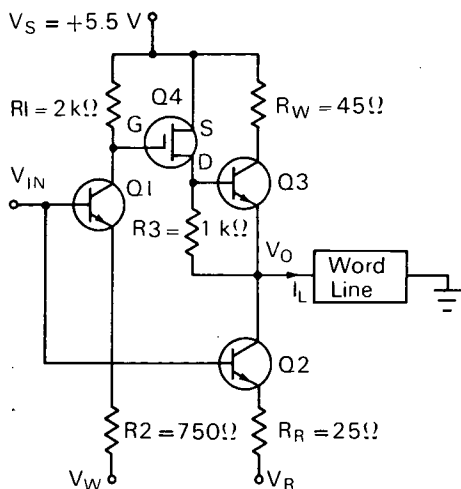


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Low-Power Integrated-Circuit Driver for Ferrite-Memory Word Lines

The problem:

Standard bidirectional current drivers utilize *npn* bipolar transistors and transformers. These circuits possess negligible quiescent power dissipation. Also, the transformers complicate integrated-circuit (IC) fabrication of these schemes. Circuits using only *npn*



Schematic of BIMOS Word-Drive Circuit

bipolar transistors consume excessive power. Although complementary bipolar circuits can provide bidirectional word-drive current pulses, fabricating high-quality *npn* and *pnp* devices on a common substrate also presents problems.

The solution:

A newly developed word-line drive circuit, realizable in IC form, generates bidirectional current pulses and consumes little power. Also, current-pulse amplitudes and rise times are independent of active-device parameters. This composite circuit uses both *npn* bipolar and *p*-channel MOS transistors (BIMOS).

How it's done:

The figure shows the new BIMOS word-driver circuit. Each driver uses three bipolar *npn* transistors (Q1, Q2, and Q3), one MOS *p*-channel device (Q4), and three internal resistors (R1, R2, and R3). Inputs consist of a positive supply line (V_S), a write line (V_W), a read line (V_R), and a write current line (V_{IN}). The emitter of Q3 and the collector of Q2 provide an output (V_O) which drives a single laminated-ferrite word line. Two external precision resistors, R_R and R_W , set the amplitude and rise time, respectively, of the read and write current pulses.

The BIMOS driver provides (1) ease of IC construction; (2) low standby power consumption; (3) bidirectional current pulses; and (4) current-pulse amplitudes and rise times independent of active-device parameters, e.g., transistor beta.

Note:

Requests for further information may be directed to:
 Technology Utilization Officer
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 Washington, D.C. 20546
 Reference: TSP70-10374

Patent status:

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